

UNITED STATES PATENT AND TRADEMARK OFFICE
(Attorney Docket No. 12734US02)

In the Application of:

Donald J. Sawdai et al.

Serial No.

EXPRESS MAIL:

EV 134753965 US

Filed:

Date:

For: **Low Leakage Schottky Diode**

October 14, 2003

Examiner:

Group Art Unit:

INFORMATION DISCLOSURE STATEMENT

Mail Stop DD
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Dear Sirs:

Pursuant to 37 C.F.R. § 1.97-1.98 and in compliance with the duty of disclosure set forth in 37 C.F.R. § 1.56, it is respectfully requested that the following references be considered in the examination of the above-identified patent application:

<u>U.S. Patent No.</u>	<u>Date</u>	<u>Name</u>
3,746,950	07-17-73	Kano et al.
4,859,616	08-22-89	Losehand et al.
5,055,890	10-08-91	Dawson et al.

Other Documents:

1. Physics of Semiconductor Devices, 2nd Edition, by S.M. Sze; John Wiley & Sons, N.Y., 1981, pages 282-311.

2. Controlled Formation of High Schottky Barriers on InP and Related Materials, by Hideki Hasegawa; May 11-15, 1998 IEEE.

3. Nearly Ideal Schottky Contacts of n-InP by Z.Q. Shi and W.A. Anderson, State University of New York at Buffalo, IPRM 1991.

4. Schottky contacts to InP, InGaAs and InAlAs, by S. Wilks, L. Jenkins, J. Morris, S. Clark and R.H. Williams, University of Wales College of Cardiff, IPRM 1991.

The above-identified reference(s) are listed on the attached Form PTO-1449 and copies are also enclosed herewith. This submission is in no way intended as an admission that the above-cited references constitute prior art. Applicant expressly retains the right to take any actions necessary to remove the above-cited references from the available prior art. Consideration of the above-identified references in the examination of the present patent application is respectfully requested.

The Commissioner is hereby authorized to charge any additional fees which may be required or credit any overpayment to Account No. 13-0017.

Respectfully submitted,



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October 14, 2003
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Form PTO-1449
(Rev. 8-83)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NO.

SERIAL NO.

12734US02

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

APPLICANT:

Donald J. Sawdai et al.

FILING DATE

GROUP
ART UNIT:

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A	3,746,950	07-17-73	Kano et al.			
	B	4,859,616	08-22-89	Losehand et al.			
	C	5,055,890	10-08-91	Dawson et al.			
	D						
	E						
	F						
	G						
	H						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AA	Physics of Semiconductor Devices, 2 nd Edition, by S.M. Sze; John Wiley & Sons, N.Y., 1981, pages 282-311.
BB	Controlled Formation of High Schottky Barriers on InP and Related Materials, by Hideki Hasegawa; May 11-15, 1998 IEEE.
CC	Nearly Ideal Schottky Contacts of n-InP by Z.Q. Shi and W.A. Anderson, State University of New York at Buffalo, IPRM 1991.
DD	Schottky contacts to InP, InGaAs and InAlAs, by S. Wilks, L. Jenkins, J. Morris, S. Clark and R.H. Williams, University of Wales College of Cardiff, IPRM 1991.

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.